Atty. Docket No. 29925/39869 Inventor: Hak-Yun Kim

Title: DRAM Cell Having MOS Capacitor and Method

for Manufacturing the Same

Sheet 1 of 5

FIG. 1 (PRIOR ART)

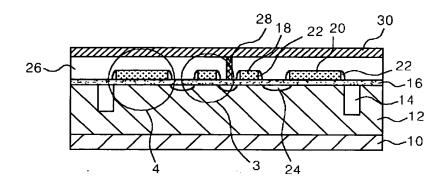
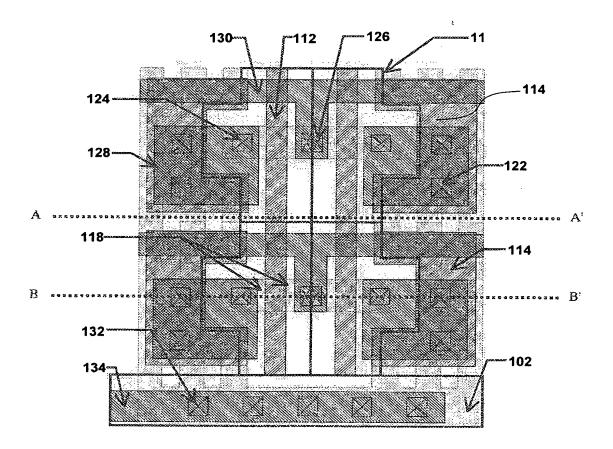


FIG. 2



Atty. Docket No. 29925/39869
Inventor: Hak-Yun Kim
Title: DRAM Cell Having MOS Capacitor and Method for
Manufacturing the Same

Sheet 2 of 5

FIG. 3

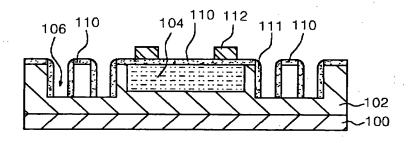


FIG. 4

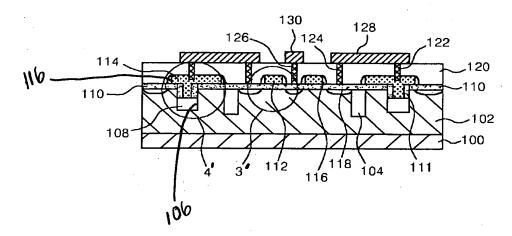
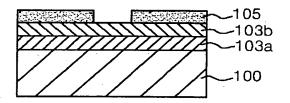


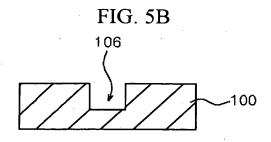
FIG. 5A



Atty. Docket No. 29925/39869 Inventor: Hak-Yun Kim

Title: DRAM Cell Having MOS Capacitor and Method for Manufacturing the Same

Sheet 3 of 5



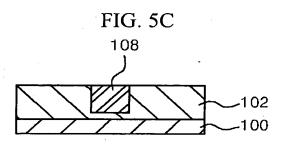


FIG. 5D

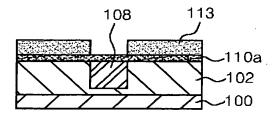
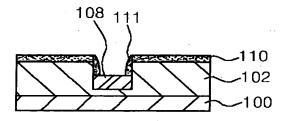


FIG. 5E



Atty. Docket No. 29925/39869 Inventor: Hak-Yun Kim

Title: DRAM Cell Having MOS Capacitor and Method for Manufacturing the Same

Sheet 4 of 5

FIG. 5F

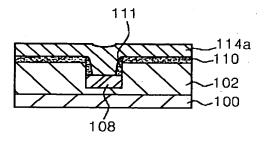


FIG. 5G

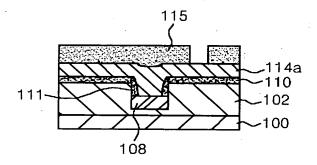
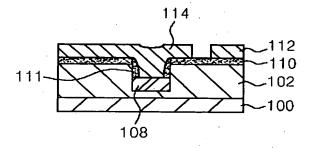


FIG. 5H



Atty. Docket No. 29925/39869 Inventor: Hak-Yun Kim Title: DRAM Cell Having MOS Capacitor and Method

for Manufacturing the Same

Sheet 5 of 5

FIG. 5I

